

The EL305 a high - power GaAs IRED mounted in a clear sidelooking package, is compact, low profile, and easy to mount.

FEATURES

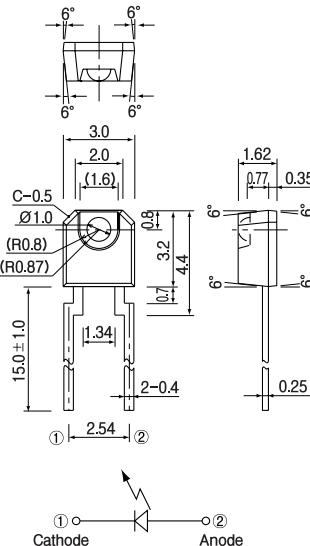
- Compact
- Low profile package
- Low - cost
- Sidelooking plastic package

APPLICATIONS

- Photointerrupters
- Optical switches
- Toys

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V _R	5	V
Forward current	I _F	50	mA
Pulse forward current ^{*1}	I _{FP}	0.5	A
Power dissipation	P _D	75	mW
Operating temp.	T _{opr.}	- 25 ~ +85	
Storage temp.	T _{stg.}	- 30 ~ +85	
Soldering temp. ^{*2}	T _{sol.}	240	

*1. pulse width : tw 100 μ sec.period : T=10msec.

*2. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

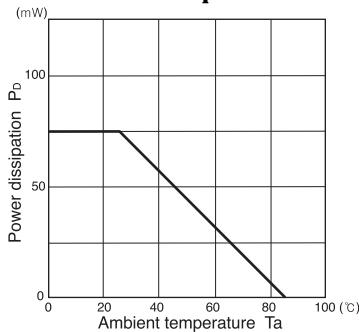
(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V _F	I _F =20mA		1.2	1.5	V
Reverse current	I _R	V _R =5V			10	μA
Capacitance	C _t	f=1MHz		25		pF
Radiant intensity	P _O	I _F =20mA		1.0		mW/sr
Peak emission wavelength	λ	I _F =20mA		940		nm
Spectral bandwidth 50%		I _F =20mA		50		nm
Half angle			± 20			deg.

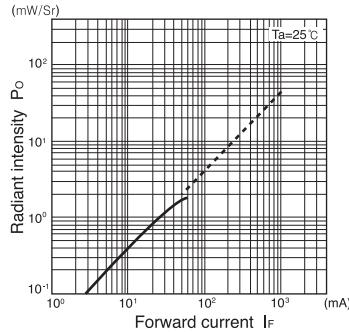
Infrared Emitting Diodes(GaAs)

EL305

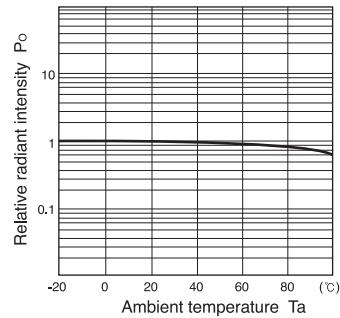
**Power dissipation Vs.
Ambient temperature**



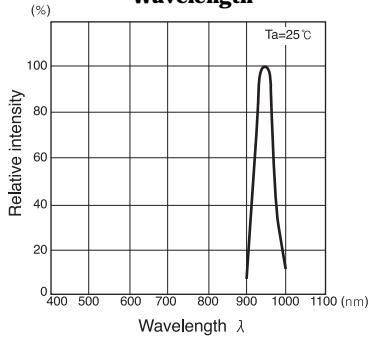
**Radiant intensity Vs.
Forward current**



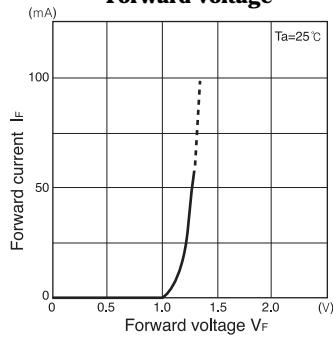
**Relative radiant intensity Vs.
Ambient temperature**



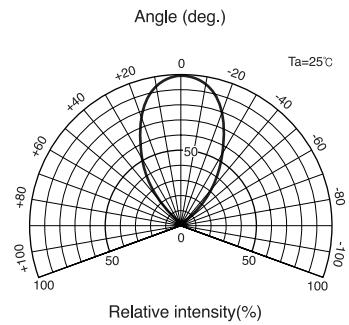
**Relative intensity Vs.
Wavelength**



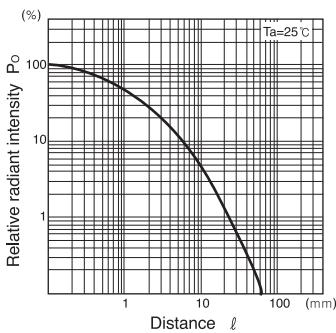
**Forward current vs.
Forward voltage**



Radiant Pattern



**Relative radiant intensity Vs.
Distance**



Relative radiant intensity Vs.
Distance test method

